

Table S1. Discharge capacities normalized to those obtained at a 0.2C rate from four Cells A and four Cells B measured at both room temperature and $-10\text{ }^{\circ}\text{C}$. All numbers are in %. SD denotes standard deviation.

Cell #	Room Temperature				$-10\text{ }^{\circ}\text{C}$			
	1C	2C	5C	10C	1C	2C	5C	10C
Cell A1	95.0	94.6	91.6	87.5	47.6	44.1	1.8	0.8
Cell A2	97.3	96.5	92.1	88.1	49.0	45.4	2.0	0.9
Cell A3	96.6	95.9	91.3	87.3	49.3	46.4	2.0	0.8
Cell A4	95.9	95.6	91.3	87.3	50.0	46.0	1.8	0.8
Average A	96.2	95.7	91.6	87.6	49.0	45.5	1.9	0.8
SD A	0.9	0.8	0.4	0.4	1.0	1.0	0.1	0.05
Cell B1	88.2	88.5	85.5	82.0	51.9	50.5	5.8	1.1
Cell B2	88.7	89.1	86.5	84.4	51.7	50.5	5.7	1.1
Cell B3	88.8	89.0	85.9	83.7	50.2	48.6	5.7	1.3
Cell B4	91.9	92.0	89.0	86.2	52.5	50.4	5.2	1.2
Average B	89.4	89.7	86.7	84.1	51.6	50.0	5.6	1.2
SD B	1.7	1.6	1.6	1.7	1.0	0.9	0.3	0.1

Table S2. Ohmic resistances (R_0 in Ω), surface charge-transfer resistances (R_{ct} in Ω), and double-layer capacitances (C in Farad) from Cells A and B measured at both room temperature (RT) and $-10\text{ }^{\circ}\text{C}$. SD denotes standard deviation.

Cell #	R_0 at RT	R_{ct} at RT	C at RT	R_0 at $-10\text{ }^{\circ}\text{C}$	R_{ct} at $-10\text{ }^{\circ}\text{C}$	C at $-10\text{ }^{\circ}\text{C}$
Cell A1	0.00164	0.00546	18.55	-	-	-
Cell A2	0.00170	0.00561	18.88	0.00333	0.04973	18.83
Cell A3	0.00159	0.00551	17.91	0.00335	0.05010	18.80
Cell A4	0.00210	0.00560	17.49	0.00351	0.05027	18.00
Average A	0.00176	0.00554	18.21	0.00340	0.05003	18.54
SD A	0.00023	0.00007	0.62	0.00010	0.00028	0.47
Cell B1	0.00187	0.00226	23.34	0.00287	0.02025	21.81
Cell B2	0.00192	0.00246	21.78	0.00297	0.01904	21.25
Cell B3	0.00227	0.00242	21.24	0.00350	0.02094	21.76
Cell B4	0.00191	0.00202	25.62	0.00313	0.01918	22.85
Average B	0.00199	0.00229	23.00	0.00311	0.01985	22.92
SD B	0.00019	0.00020	1.96	0.00027	0.00090	0.67